

L Number	Hits	Search Text	DB	Time stamp
-	2	("6489237").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	7761	"mold compound" or "mold resin"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:56
-	696	passivation and mounting and (etch\$3 or pattern\$3) and (polysilicon or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	8	("mold compound" or "mold resin") and (passivation and mounting and (etch\$3 or pattern\$3) and (polysilicon or polycrystalline))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	5423	oxide and mount\$3 and (etch\$3 and pattern\$3) and (polysilicon or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:21
-	21	("mold compound" or "mold resin") and (oxide and mount\$3 and (etch\$3 and pattern\$3) and (polysilicon or polycrystalline))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:21
-	16	((("mold compound" or "mold resin") and (oxide and mount\$3 and (etch\$3 and pattern\$3) and (polysilicon or polycrystalline))) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:56
-	21888	(opening or hole or trench or recess) with (polysilicon or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:29
-	30	((opening or hole or trench or recess) with (polysilicon or polycrystalline)) and ("mold compound" or "mold resin")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:29
-	1	((opening or hole or trench or recess) with (polysilicon or polycrystalline)) with ("mold compound" or "mold resin")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:29
-	13	((("6489237") or ("6329288") or ("6294454") or ("5048179") or ("6593649") or ("6277672")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:32
-	6	((("6489237") or ("6329288") or ("6294454") or ("5048179") or ("6593649") or ("6277672")).PN.	USPAT	2004/04/13 15:33
-	441758	semiconductor near device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:33
-	1114	(semiconductor near device) same dens\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:34

-	145	((semiconductor near device) same dens\$2) and (deposit\$3 same (polycrystalline or polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:34
-	57	((semiconductor near device) same dens\$2) and (deposit\$3 same ((polycrystalline or polysilicon) same (recess or hole or opening or trench)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 15:56
-	53	((semiconductor near device) same dens\$2) and (deposit\$3 same ((polycrystalline or polysilicon) same (recess or hole or opening or trench))) not (@ad>20020128 or @rlad>20020128)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 16:02
-	0	((semiconductor near device) same dens\$2) and (deposit\$3 same ((polycrystalline or polysilicon) same (recess or hole or opening or trench))) not (@ad>20020128 or @rlad>20020128) and (CTE or "coefficient of thermal expansion")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 16:03
-	2107	((438/124) or (438/127) or (438/129)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	0	((438/124) or (438/127) or (438/129)).CCLS.) and ("mold compound" or "mold resin") and (passivation and mounting and (etch\$3 or pattern\$3) and (polysilicon or polycrystalline))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	3	((438/124) or (438/127) or (438/129)).CCLS.) and (passivation and mounting and (etch\$3 or pattern\$3) and (polysilicon or polycrystalline))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:55
-	6809	((438/124) or (438/127) or (438/129)).CCLS.) and "mold compound" or "mold resin"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:56
-	189	((438/124) or (438/127) or (438/129)).CCLS.) and ("mold compound" or "mold resin")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 15:56